General purpose PIN diode

Features

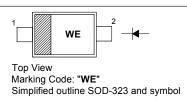
- Low forward resistance
- Low capacitance

Applications

• General RF applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol Value		Unit
Reverse Voltage	V_R	50	V
Continuous Forward Current	I _F	50	mA
Total Power Dissipation (T _S = 90 °C)	P _{tot}	500	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Electrical Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I _F = 50 mA	V _F	-	1.1	V
Reverse Current at $V_R = 50 \text{ V}$	I _R	-	100	nA
Reverse Voltage at I _R = 10 μA	V _R	50	-	V
Diode Capacitance at $V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$ at $V_R = 5 \text{ V}$, $f = 1 \text{ MHz}$	C _d		0.55 0.35	pF
Forward Resistance at I_F = 0.5 mA, f = 100 MHz at I_F = 1 mA, f = 100 MHz at I_F = 10 mA, f = 100 MHz	r _D	- - -	40 25 5	Ω

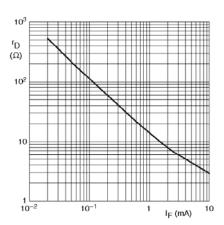






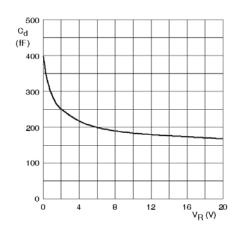






f = 100 MHz; T_j = 25 °C.

Forward resistance as a function of forward current; typical values.



f = 1 MHz; T_j = 25 °C.

Diode capacitance as a function of reverse voltage; typical values.



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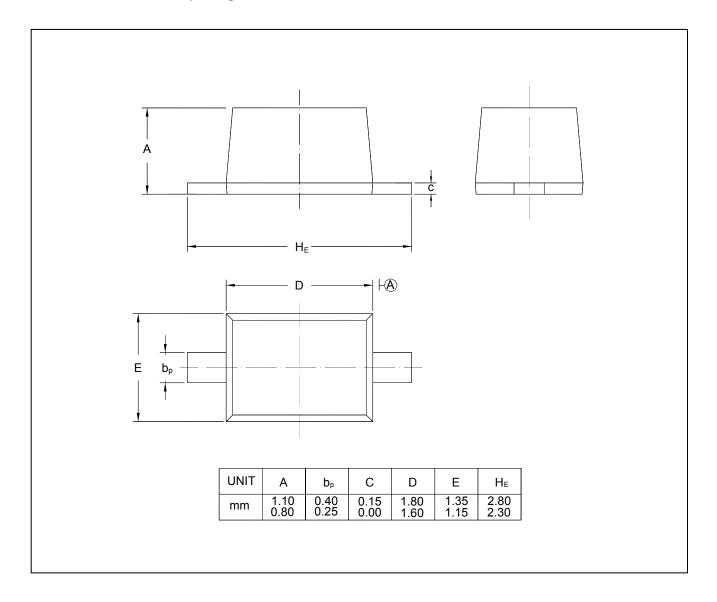




PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



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